

N-Channel 650 V (D-S) MOSFET

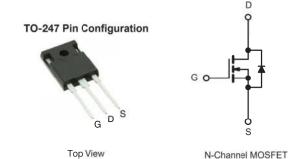
PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (mΩ)(Typ.)	I _D (A)	Q _g (Typ.)
650	60 at V _{GS} = 10 V	50	77 nC

FEATURES

- DT-Trench Power MOSFET
- 100 % Rg and UIS tested
- Low Gate Charge
- Low $R_{DS(ON)}(Typ 60m\Omega)@V_{GS}=10 V$

APPLICATIONS

- High efficient switched mode power supplies
- Adapter/charger
- Server Power
- LED Lighting



ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	650	V	
Gate-Source Voltage		V _{GS} ± 30			
Continuous Dusin Comment /T 150 °C)	T _C = 25 °C		50		
Continuous Drain Current (T _J = 150 °C)	T _C = 100 °C	- I _D	32		
Pulsed Drain Current (t = 100 μs)		I _{DM}	150	Α Α	
Avalanche Current	L = 0.1 mH	I _{AS}	45		
Single Avalanche Energy ^a	L=0.11IIII	E _{AS}	906	mJ	
Maximum Power Dissipation ^a	T _C = 25 °C	P _D	339	W	
	T _C = 125 °C	T PD	88		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +150	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	35	°C/W	
Junction-to-Case (Drain)	R _{thJC}	0.4]	

Notes

- a. Duty cycle \leq 1 %.
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR4 material).

Rev. 1. 0



PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	650	-	-	V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	2	-	4	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current	1	V _{DS} = 650 V, V _{GS} = 0 V	-	-	1	μА
Zero date voltage brain ourient	IDSS	$V_{DS} = 480 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 100 ^{\circ}\text{C}$	-	-	100	
Drain-Source On-State Resistance a	R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	-	60	76	mΩ
Forward Transconductance a	9 _{fs}	$V_{DS} = 5 \text{ V}, I_{D} = 20 \text{ A}$	-	40	-	S
Dynamic ^b				<u> </u>		
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 300 V, f = 1 MHz	-	3060	-	pF
Output Capacitance	C _{oss}		-	105	-	
Reverse Transfer Capacitance	C _{rss}		-	3	-	
Total Gate Charge ^c	Qg	V _{DS} = 30 V, V _{GS} = 10 V, I _D = 20 A	-	77	-	nC
Gate-Source Charge ^c	Q _{gs}		-	19	-	
Gate-Drain Charge ^c	Q _{gd}		-	36	-	
Gate Resistance	R _g	f = 1 MHz	-	1.0	-	Ω
Turn-On Delay Time ^c	t _{d(on)}		-	35	-	
Rise Time ^c	t _r	$V_{DD} = 300 \text{ V}, R_L = 120 \Omega$ $I_D = 20 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 20 \Omega$	-	72	-	
Turn-Off Delay Time ^c	t _{d(off)}		-	88	-	ns ns
Fall Time ^c	t _f		-	60	-	
Drain-Source Body Diode Ratings ar	nd Characteris	stics ^b (T _C = 25 °C)				
Continuous Source Current	Is	T _C = 25 °C	-	-	50	Α
Pulsed Current (t = 100 μs)	I _{SM}		-	-	150	Α
Forward Voltage ^a	V _{SD}	$I_F = 20 \text{ A}, V_{GS} = 0 \text{ V}$	-	-	1.2	V
Reverse Recovery Time	t _{rr}		-	388	-	ns
Reverse Recovery Charge	Q _{rr}	$I_F = 20 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$	-	6.5	-	μC

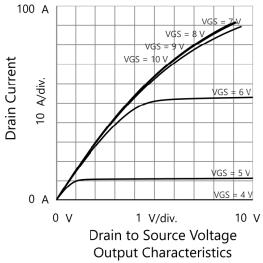
Notes

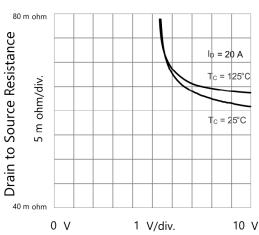
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

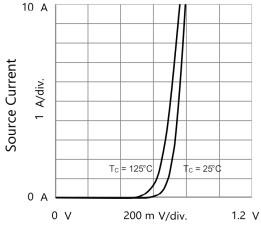


TYPICAL CHARACTERISTICS ($T_A = 25 \, ^{\circ}C$, unless otherwise noted)

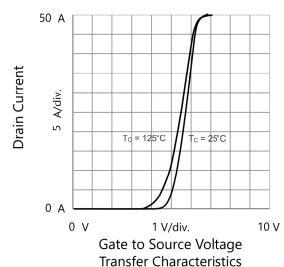


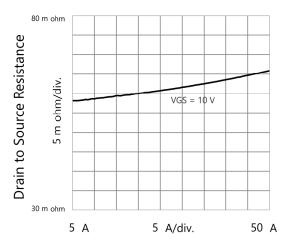


Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage

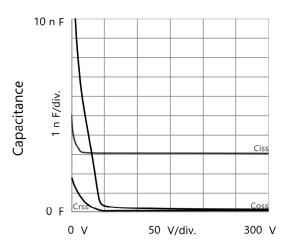


Source to Drain Voltage Body Diode Forward Characteristics



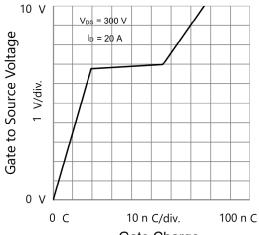


Drain Current
Drain to Source Resistance vs. Drain Current

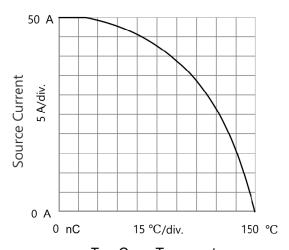


Drain to Source Voltage Capacitances

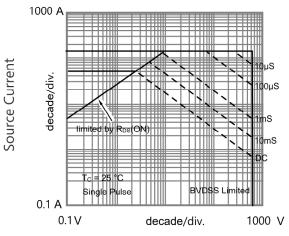
TYPICAL CHARACTERISTICS (T = 25 °C, unless otherwise noted)



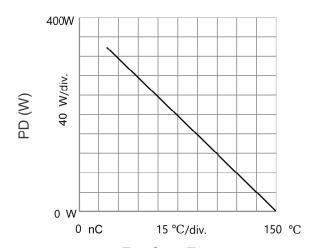
Gate Charge
Gate to Source Voltage vs. GateCharge



T_C - Case Temperature
Current Derating

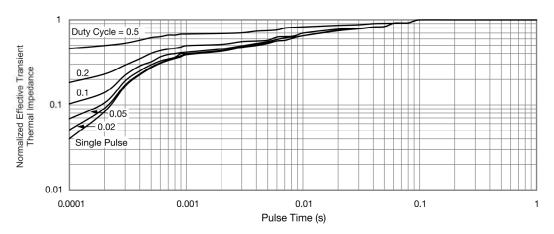


Source to Drain Voltage Safe Operating Area, Junction-to-Ambient



T_C - Case Temperature
Power Derating

THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction to Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.





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